NTD5803N

Power MOSFET
40 V, 76 A, Single N−Channel, DPAK

Features
- Low $R_{DS(on)}$
- High Current Capability
- Avalanche Energy Specified
- These are Pb−Free Devices

Applications
- CCFL Backlight
- DC Motor Control
- Class D Amplifier
- Power Supply Secondary Side Synchronous Rectification

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	40	V
Gate−to−Source Voltage − Continuous			V_{GS}	±20	V
Gate−to−Source Voltage − Non−Repetitive (t_p < 10 μS)			V_{GS}	±30	V
Continuous Drain Current ($R_{\theta JC}$) (Note 1)	Steady State	T_C = 25°C	I_D	76	A
		T_C = 100°C		54	
Power Dissipation ($R_{\theta JC}$) (Note 1)		T_C = 25°C	P_D	83	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	228	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 175	°C
Source Current (Body Diode)			I_S	76	A
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 50 V, V_{GS} = 10 V, R_G = 25 Ω, $I_{L(pk)}$ = 40 A, L = 0.3 mH)			E_{AS}	240	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	1.8	°C/W
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	64	

1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces.

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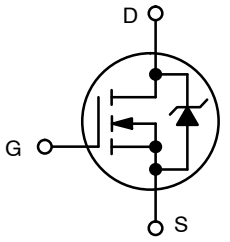
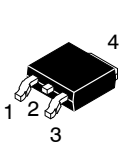
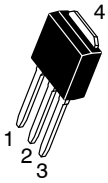
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	10.1 mΩ @ 5.0 V	54 A
	7.2 mΩ @ 10 V	76 A



N−CHANNEL MOSFET

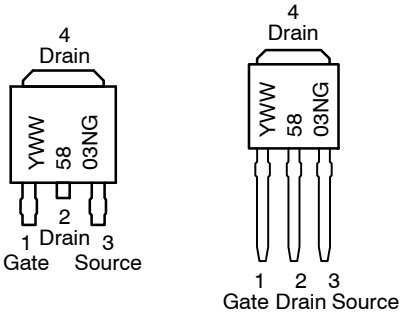


DPAK
CASE 369C
(Surface Mount)
STYLE 2



DPAK
CASE 369D
(Straight Lead)
STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENT



Y = Year
WW = Work Week
5803N = Device Code
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		40			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				40		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V	T_J = 25°C			1.0	μA
			T_J = 150°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.5		3.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−7.4		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 50 A			4.9	7.2	mΩ
		V_{GS} = 5.0 V, I_D = 30 A			6.7	10.1	
Forward Transconductance	gFS	V_{DS} = 15 V, I_D = 15 A			13.6		S
CHARGES, CAPACITANCES AND GATE RESISTANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			3220		pF
Output Capacitance	C_{oss}				390		
Reverse Transfer Capacitance	C_{rss}				270		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 20 V, I_D = 50 A			51		nC
Threshold Gate Charge	$Q_{G(TH)}$				3.8		
Gate−to−Source Charge	Q_{GS}				12.7		
Gate−to−Drain Charge	Q_{GD}				12.7		
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 32 V, I_D = 50 A, R_G = 2.0 Ω			12.6		ns
Rise Time	t_r				21.4		
Turn−Off Delay Time	$t_{d(off)}$				28.3		
Fall Time	t_f				6.6		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 30 A	T_J = 25°C		0.88	1.2	V
			T_J = 150°C		0.73		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIs/dt = 100 A/μs, I_S = 30 A			27.2		ns
Charge Time	ta				14		
Discharge Time	tb				13.2		
Reverse Recovery Charge	Q_{RR}				17		nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Order Number	Package	Shipping†
NTD5803NG	DPAK (Straight Lead) (Pb−Free)	75 Units / Rail
NTD5803NT4G	DPAK (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

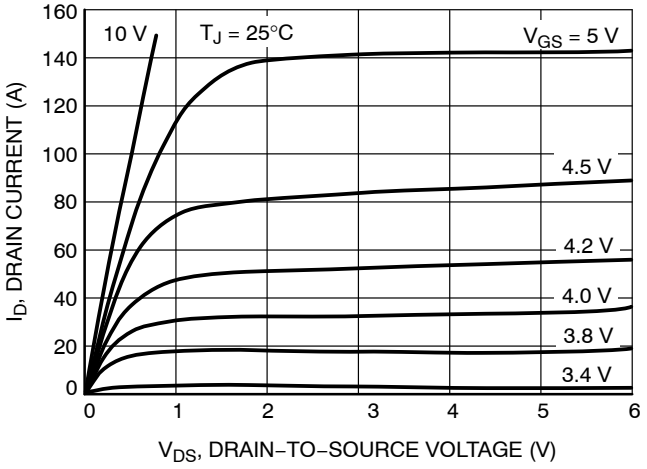


Figure 1. On−Region Characteristics

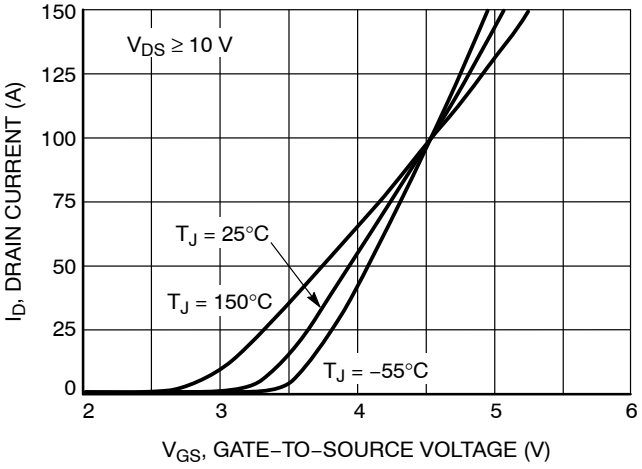


Figure 2. Transfer Characteristics

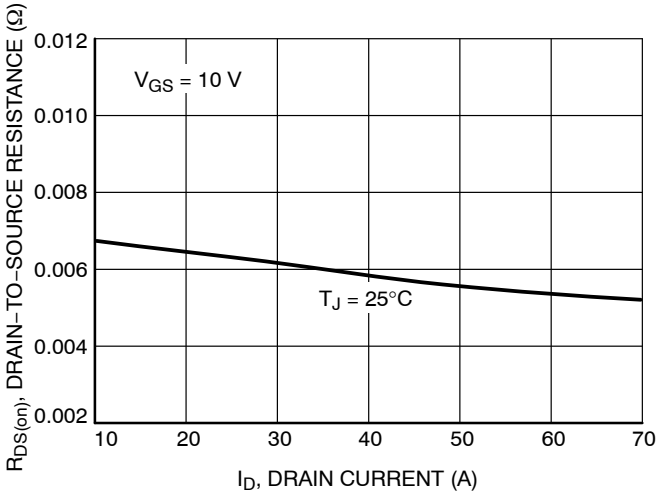


Figure 3. On−Resistance vs. Drain Current

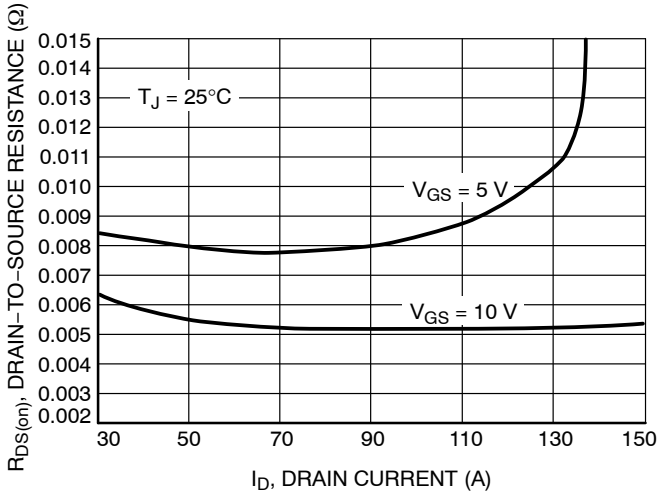


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

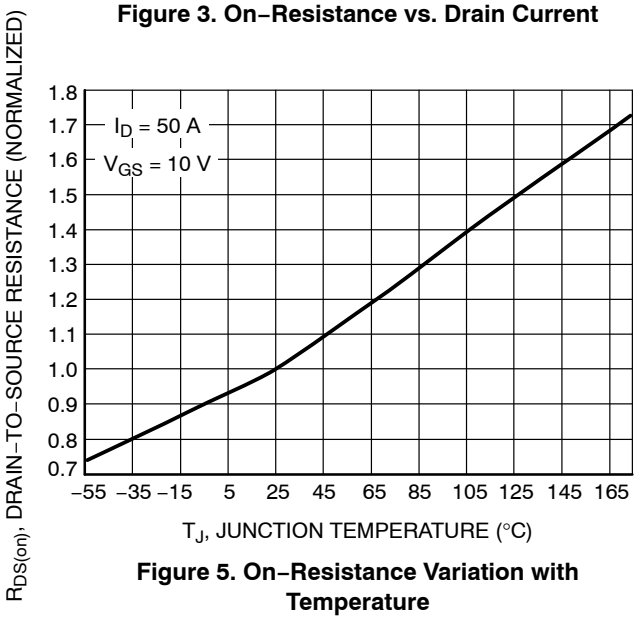


Figure 5. On−Resistance Variation with Temperature

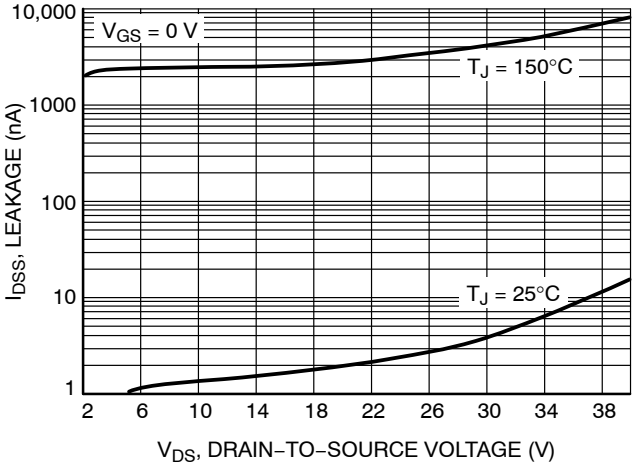


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

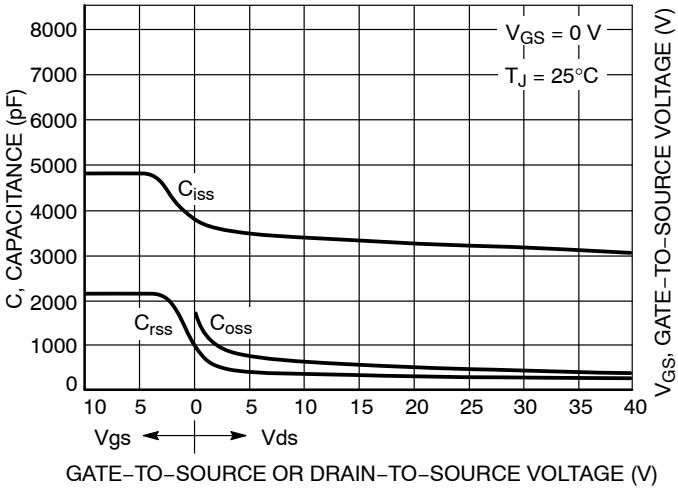


Figure 7. Capacitance Variation

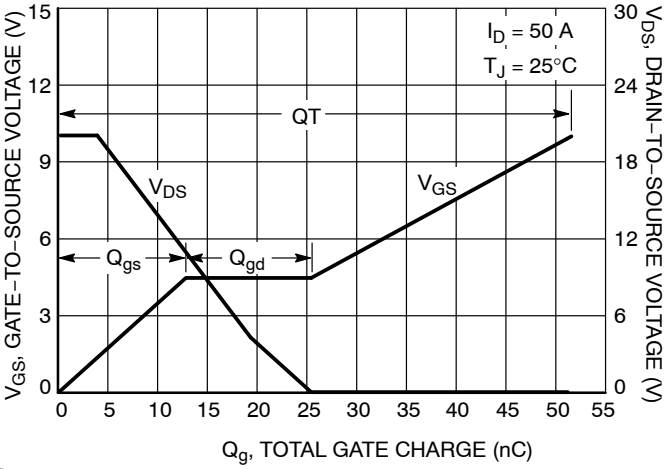


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

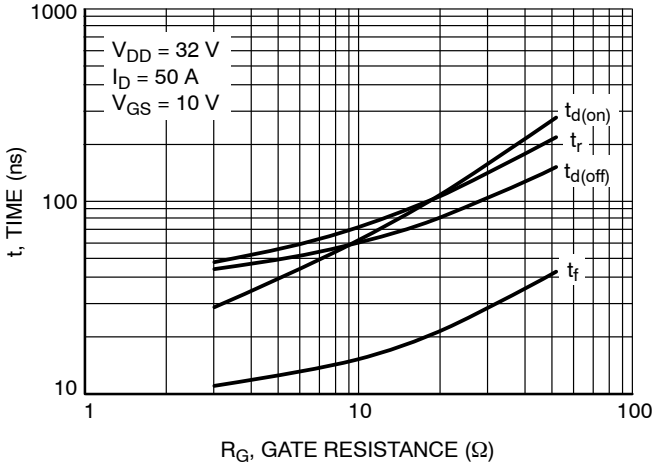


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

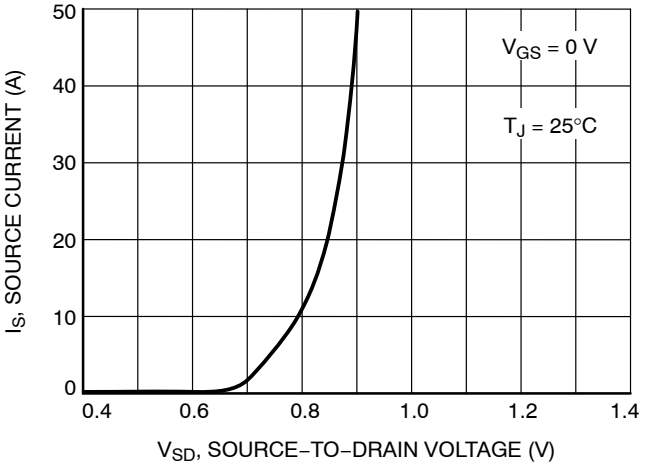
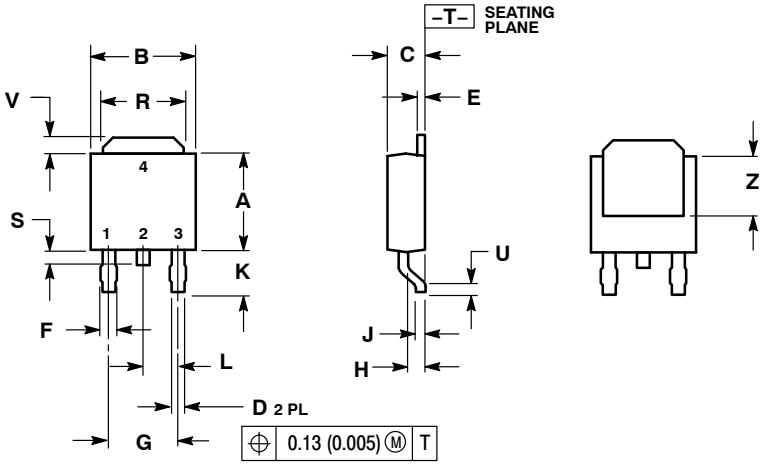


Figure 10. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

DPAK
CASE 369C−01
ISSUE O

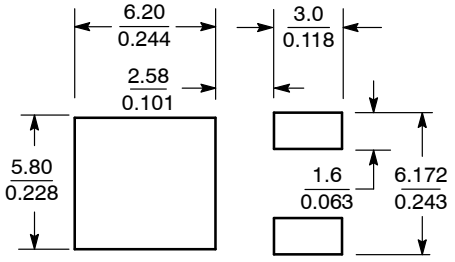


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	−−−	0.51	−−−
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*

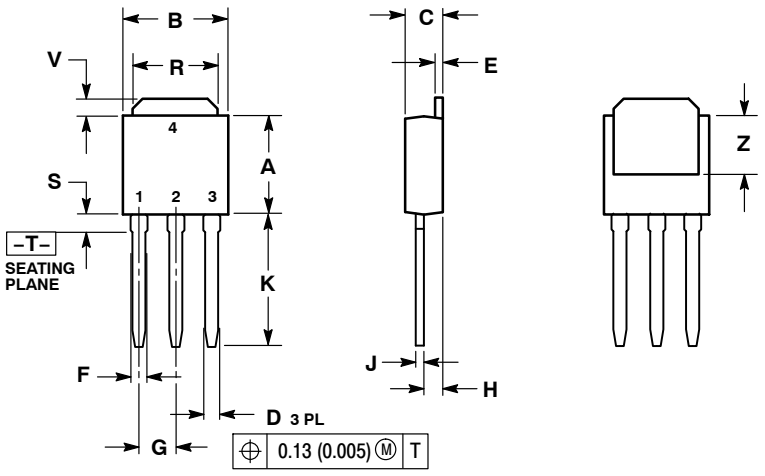


SCALE 3:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

DPAK
CASE 369D−01
ISSUE B



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D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
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NTD5803N/D